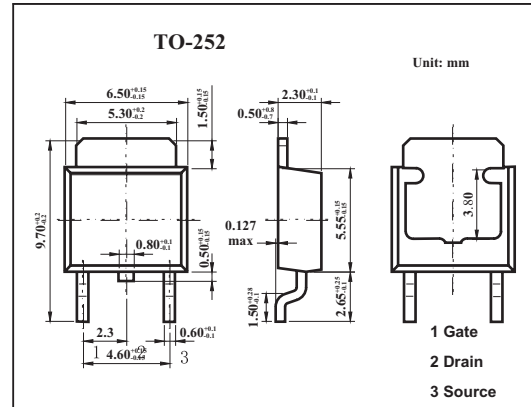


MOS Field Effect Transistor

2SK3638

■ Features

- Low on-state resistance
 $R_{DS(on)1} = 8.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 32 \text{ A)}$
 $R_{DS(on)2} = 15 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 18 \text{ A)}$
- Low C_{iss} : $C_{iss} = 1100 \text{ pF TYP.}$
- Built-in gate protection diode



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	20	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	± 64	A
	I_{dp}^*	± 220	A
Power dissipation	P_D	$T_c=25^\circ\text{C}$	36
		$T_A=25^\circ\text{C}$	1.0
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=20\text{V}, V_{GS}=0$			10	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 20\text{V}, V_{DS}=0$			± 10	μA
Gate cut off voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}, I_D=1\text{mA}$	1.5		2.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10\text{V}, I_D=32\text{A}$	12	25		S
Drain to source on-state resistance	$R_{DS(on)1}$	$V_{GS}=10\text{V}, I_D=32\text{A}$		6.8	8.5	$\text{m}\Omega$
	$R_{DS(on)2}$	$V_{GS}=4.5\text{V}, I_D=18\text{A}$		10	15	$\text{m}\Omega$
Input capacitance	C_{iss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$		1100		pF
Output capacitance	C_{oss}			450		pF
Reverse transfer capacitance	C_{rss}			170		pF
Turn-on delay time	t_{on}	$I_D=32\text{A}, V_{GS(on)}=10\text{V}, R_G=0\Omega, V_{DD}=10\text{V}$		10		ns
Rise time	t_r			4.3		ns
Turn-off delay time	t_{off}			35		ns
Fall time	t_f			9.7		ns
Total Gate Charge	Q_G	$V_{DD} = 16\text{V}$		22		nC
Gate to Source Charge	Q_{GS}	$V_{GS} = 10 \text{ V}$		4.3		nC
Gate to Drain Charge	Q_{GD}	$I_D = 64\text{A}$		5.1		nC